



IR30DDR..L SERIES

HIGH POWER RECTIFIER DIODES

- Junction Size: 30 mm Diameter
- V_{RRM} Class: 400 to 1600 V
- Passivation Process: Diffused Junction

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1.28V	$T_J = 25^\circ\text{C}$, $I_F = 1000\text{ A}$
V_{RRM} Reverse Breakdown Voltage Range	400 to 1600 V	$T_J = 150^\circ\text{C}$, $I_{RRM} = 20\text{ mA}$

Mechanical Characteristics

Nominal Back Metal Composition	Al - Ni - Au
Nominal Front Metal Composition	Nickel plate Molibdenum disc
Chip Dimensions	30 mm diameter (see drawing)
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

IR30DDR..L Series

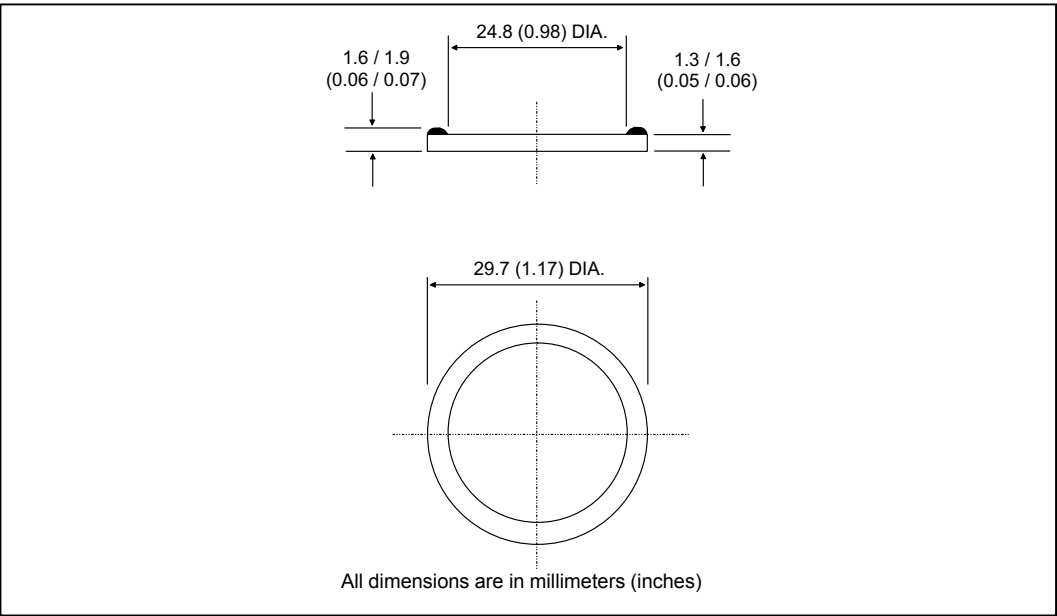
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International
IR Rectifier

Ordering Information Table

Device Code						
IR30DDR16L 1 2 3 4 5 6 7						
1	- International Rectifier device					
2	- Chip Dimension in Millimeters					
3	- Device identifier between chip with same diameter					
4	- Type of Device: D = Standard Recovery Diode					
5	- Passivation: R = Rubber for all junctions					
6	- Voltage code: Code x 100 = V_{RRM}					
7	- Metallization: L = Nickel plate Molybdenum disc (Anode) Al - Ni - Au (Cathode)					
						Available Class 04 = 400 V 08 = 800 V 10 = 1000 V 12 = 1200 V 16 = 1600 V

Outline Table



Data and specifications subject to change without notice.
This product has been designed and qualified for Industrial Level.
Qualification Standards can be found on IR's Web site.

International
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